



Micro Commercial Components  
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# 2SB772

## Features

- Capable of 1.25Watts of Power Dissipation.
- Collector-current 3.0A
- Collector-base Voltage 40V
- Operating and storage junction temperature range: -55°C to +150°C

## PNP Silicon Plastic-Encapsulate Transistor

### Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
<b>OFF CHARACTERISTICS</b>				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ( $I_C=10mA$ , $I_E=0$ )	30	---	Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ( $I_C=100\mu A$ , $I_E=0$ )	40	---	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ( $I_E=100\mu A$ , $I_C=0$ )	5.0	---	Vdc
$I_{CBO}$	Collector Cutoff Current ( $V_{CB}=40V$ , $I_E=0$ )	---	1.0	$\mu A$
$I_{CEO}$	Collector Cutoff Current ( $V_{CE}=30V$ , $I_B=0$ )	---	1.0	$\mu A$
$I_{EBO}$	Emitter Cutoff Current ( $V_{EB}=6.0V$ , $I_C=0$ )	---	1.0	$\mu A$

### ON CHARACTERISTICS

$h_{FE(1)}$	DC Current Gain ( $I_C=1.0A$ , $V_{CE}=2.0V$ )	60	400	---
$h_{FE(2)}$	DC Current Gain ( $I_C=100mA$ , $V_{CE}=2.0V$ )	32	---	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ( $I_C=2.0A$ , $I_E=0.2A$ )	---	0.5	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ( $I_C=2.0A$ , $I_E=0.2A$ )	---	2.0	Vdc

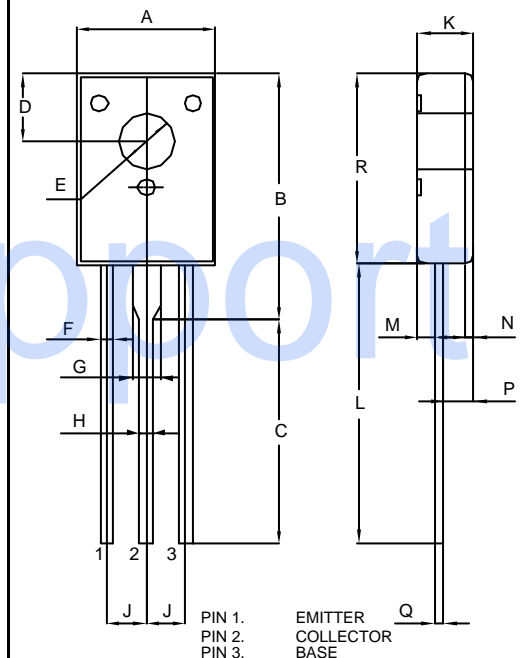
### SMALL-SIGNAL CHARACTERISTICS

$f_T$	Transistor Frequency ( $I_C=0.1A$ , $V_{CE}=5.0V$ , $f=10MHz$ )	50	---	MHz
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### CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

### TO-18



### DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.30	0.33	7.70	8.30	
B		0.56		14.20	
C	0.50	0.53	12.76	13.36	
D	0.15	0.16	3.80	4.0	
E	0.12	0.13	3.10	3.30	
F	0.025	0.033	0.65	0.85	
G	0.06	0.07	1.50	1.70	
H	0.025	0.033	0.65	0.85	
J	0.08	0.10	2.08	2.48	
K	0.12	0.14	3.05	3.45	
L	0.63	0.64	15.90	16.30	
M		0.04		1.0	
N		0.02		0.5	
P	0.06	0.08	1.55	1.95	
Q	0.018	0.023	0.45	0.60	
R	0.43	0.44	10.80	11.20	